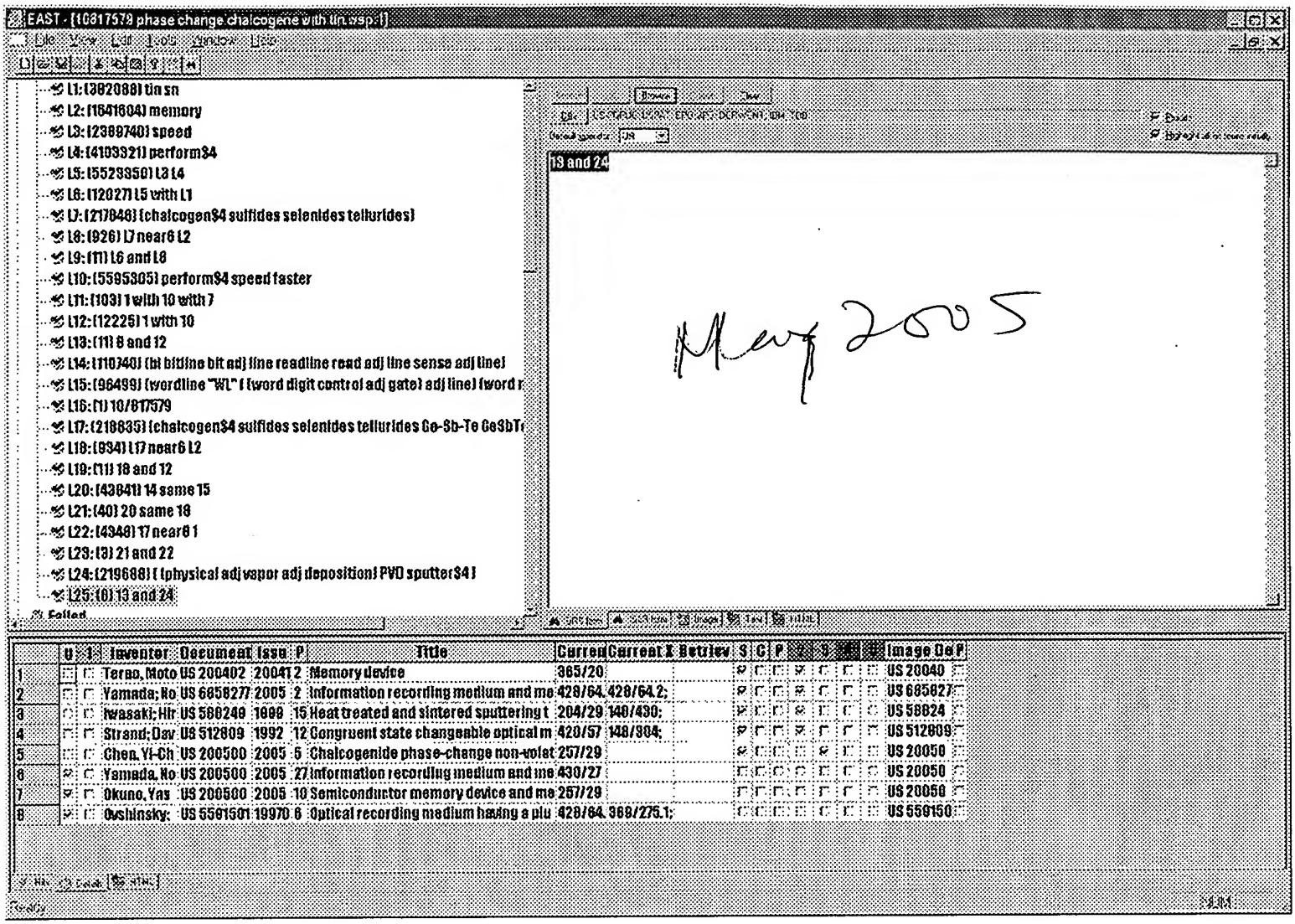
EAST - [10817579 phase change chalcogene with tin sn 1]
File View Edit Tools Window Help
L1: (3820888) tin sn
L2: (11641604) memory
L3: (2389740) speed
L4: (4109321) perform$4
L5: (5529350) l3 l4
L6: (12027) L5 with L1
L7: (217848) (chalcogen$4 sulfides selenides tellurides)
L8: (926) L7 near6 L2
L9: (11) L6 and L8
L10: (5595305) perform$4 speed faster
L11: (103) 1 with 10 with 7
L12: (12225) 1 with 10
L13: (11) 8 and 12
L14: (110340) (bl bitline bit adj line readline read adj line sense adj line)
L15: (96499) (wordline "WL" ((word digit control adj gate) adj line) (word
L16: (1) 10/817579
L17: (218835) (chalcogen$4 sulfides selenides tellurides Ge-Sb-Te GeSbT
L18: (934) L17 near6 L2
L19: (11) 18 and 12
L20: (43841) 14 same 15
L21: (40) 20 same 18
L22: (4948) 17 near6 1
L23: (3) 21 and 22
L24: (219688) ((physical adj vapor adj deposition) PVD sputter$4)
L25: (0) 13 and 24
Failed
19 and 24
May 2005
U I Inventor Document Issu P Title Current Current X Retriev S C P S S Image Do P
1 Terao, Moto US 200402 20041 2 Memory device 365/20 US 20040
2 Yamada; No US 6858277 2005 2 Information recording medium and me 428/64; 428/64.2; US 685827
3 Iwasaki; Hir US 588249 1999 15 Heat treated and sintered sputtering t 204/29 148/430; US 58824
4 Strand; Dav US 512809 1992 12 Congruent state changeable optical m 420/57 148/304; US 512809
5 Chen, Yi-Ch US 200500 2005 6 Chalcogenide phase-change non-volat 257/29 US 20050
6 Yamada, No US 200500 2005 27 Information recording medium and me 430/27 US 20050
7 Okuno, Yas US 200500 2005 10 Semiconductor memory device and me 257/29 US 20050
8 Ovshinsky; US 5591501 19970 6 Optical recording medium having a plu 428/64; 369/275.1; US 559150